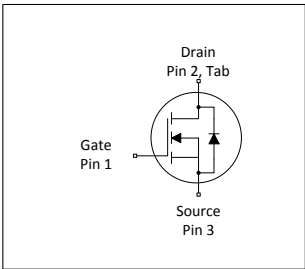
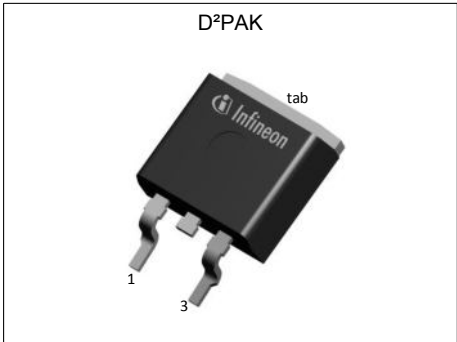


MOSFET

OptiMOS™ 5 Linear FET, 150 V

Features

- Ideal for hot-swap and e-fuse applications
- Very low on-resistance $R_{DS(on)}$
- Wide safe operating area SOA
- N-channel, normal level
- 100% avalanche tested
- Pb-free plating; RoHS compliant
- Qualified according to JEDEC¹⁾ for target applications
- Halogen-free according to IEC61249-2-21



RoHS

Table 1 Key Performance Parameters

Parameter	Value	Unit
V_{DS}	150	V
$R_{DS(on),max}$	4.8	mΩ
I_D	150	A
I_{pulse} ($V_{DS}=56$ V, $t_p=10$ ms)	10.8	A

Type / Ordering Code	Package	Marking	Related Links
IPB048N15N5LF	PG-TO263-3	048N15LF	-

¹⁾ J-STD20 and JESD22

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1 Maximum ratings

at $T_C=25\text{ °C}$, unless otherwise specified

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current ¹⁾	I_D	-	-	150 115 18	A	$V_{GS}=10\text{ V}$, $T_C=25\text{ °C}$ $V_{GS}=10\text{ V}$, $T_C=100\text{ °C}$ $V_{GS}=10\text{ V}$, $T_C=25\text{ °C}$, $R_{thJA}=40\text{K/W}^{2)}$
Pulsed drain current ³⁾	$I_{D,pulse}$	-	-	600	A	$T_C=25\text{ °C}$
Avalanche energy, single pulse ⁴⁾	E_{AS}	-	-	30	mJ	$I_D=40\text{ A}$, $R_{GS}=25\text{ }\Omega$
Gate source voltage	V_{GS}	-20	-	20	V	-
Power dissipation	P_{tot}	-	-	313	W	$T_C=25\text{ °C}$
Operating and storage temperature	T_j , T_{stg}	-55	-	150	°C	-

2 Thermal characteristics

Table 3 Thermal characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	R_{thJC}	-	0.25	0.4	K/W	-
Device on PCB, minimal footprint	R_{thJA}	-	-	62	K/W	-
Device on PCB, 6 cm ² cooling area ²⁾	R_{thJA}	-	-	40	K/W	-

¹⁾ Rating refers to the product only with datasheet specified absolute maximum values, maintaining case temperature as specified. For other case temperatures please refer to Diagram 2. De-rating will be required based on the actual environmental conditions.

²⁾ Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.

³⁾ See Diagram 3 for more detailed information

⁴⁾ See Diagram 13 for more detailed information

3 Electrical characteristics

at $T_j=25\text{ °C}$, unless otherwise specified

Table 4 Static characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	150	-	-	V	$V_{GS}=0\text{ V}$, $I_D=1\text{ mA}$
Gate threshold voltage	$V_{GS(th)}$	3.3	4.1	4.9	V	$V_{DS}=V_{GS}$, $I_D=255\text{ }\mu\text{A}$
Zero gate voltage drain current	I_{DSS}	-	1 10	2 100	μA	$V_{DS}=120\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=25\text{ °C}$ $V_{DS}=120\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=125\text{ °C}$
Gate-source leakage current	I_{GSS}	-	2 -2	5 -5	μA	$V_{GS}=20\text{ V}$, $V_{DS}=0\text{ V}$ $V_{GS}=-10\text{ V}$, $V_{DS}=0\text{ V}$
Drain-source on-state resistance	$R_{DS(on)}$	-	3.9	4.8	$\text{m}\Omega$	$V_{GS}=10\text{ V}$, $I_D=100\text{ A}$
Gate resistance ¹⁾	R_G	-	25	38	Ω	-
Transconductance ¹⁾	g_{fs}	17	34	-	S	$ V_{DS} >2 I_D R_{DS(on)max}$, $I_D=100\text{ A}$

Table 5 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance ¹⁾	C_{iss}	-	290	380	pF	$V_{GS}=0\text{ V}$, $V_{DS}=75\text{ V}$, $f=1\text{ MHz}$
Output capacitance ¹⁾	C_{oss}	-	1400	1800	pF	$V_{GS}=0\text{ V}$, $V_{DS}=75\text{ V}$, $f=1\text{ MHz}$
Reverse transfer capacitance ¹⁾	C_{rss}	-	13	23	pF	$V_{GS}=0\text{ V}$, $V_{DS}=75\text{ V}$, $f=1\text{ MHz}$
Turn-on delay time	$t_{d(on)}$	-	8	-	ns	$V_{DD}=75\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=60\text{ A}$, $R_{G,ext}=1.6\text{ }\Omega$
Rise time	t_r	-	48	-	ns	$V_{DD}=75\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=60\text{ A}$, $R_{G,ext}=1.6\text{ }\Omega$
Turn-off delay time	$t_{d(off)}$	-	42	-	ns	$V_{DD}=75\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=60\text{ A}$, $R_{G,ext}=1.6\text{ }\Omega$
Fall time	t_f	-	10	-	ns	$V_{DD}=75\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=60\text{ A}$, $R_{G,ext}=1.6\text{ }\Omega$

Table 6 Gate charge characteristics²⁾

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge	Q_{gs}	-	2	-	nC	$V_{DD}=75\text{ V}$, $I_D=60\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate to drain charge	Q_{gd}	-	56	-	nC	$V_{DD}=75\text{ V}$, $I_D=60\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate charge total	Q_g	-	84	-	nC	$V_{DD}=75\text{ V}$, $I_D=60\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate plateau voltage	$V_{plateau}$	-	7	-	V	$V_{DD}=75\text{ V}$, $I_D=60\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Output charge ¹⁾	Q_{oss}	-	211	280	nC	$V_{DD}=75\text{ V}$, $V_{GS}=0\text{ V}$

¹⁾ Defined by design. Not subject to production test.

²⁾ See "Gate charge waveforms" for parameter definition

Table 7 Reverse diode

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode continuous forward current	I_S	-	-	150	A	$T_C=25\text{ °C}$
Diode pulse current	$I_{S,pulse}$	-	-	600	A	$T_C=25\text{ °C}$
Diode forward voltage	V_{SD}	-	0.93	1.2	V	$V_{GS}=0\text{ V}$, $I_F=100\text{ A}$, $T_j=25\text{ °C}$
Reverse recovery time	t_{rr}	-	60	-	ns	$V_R=75\text{ V}$, $I_F=60\text{ A}$, $di_F/dt=100\text{ A}/\mu\text{s}$
Reverse recovery charge	Q_{rr}	-	81	-	nC	$V_R=75\text{ V}$, $I_F=60\text{ A}$, $di_F/dt=100\text{ A}/\mu\text{s}$

4 Electrical characteristics diagrams

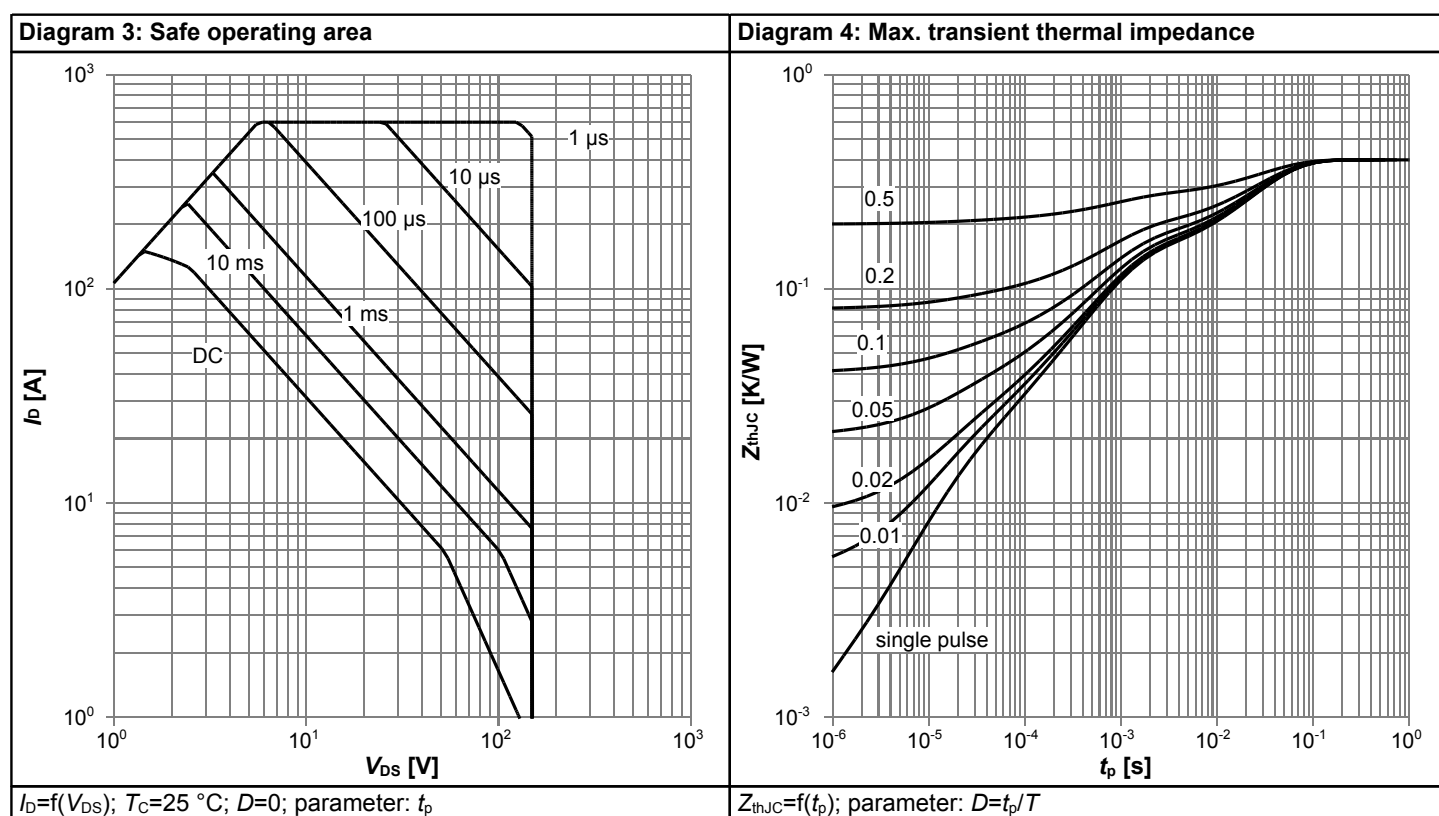
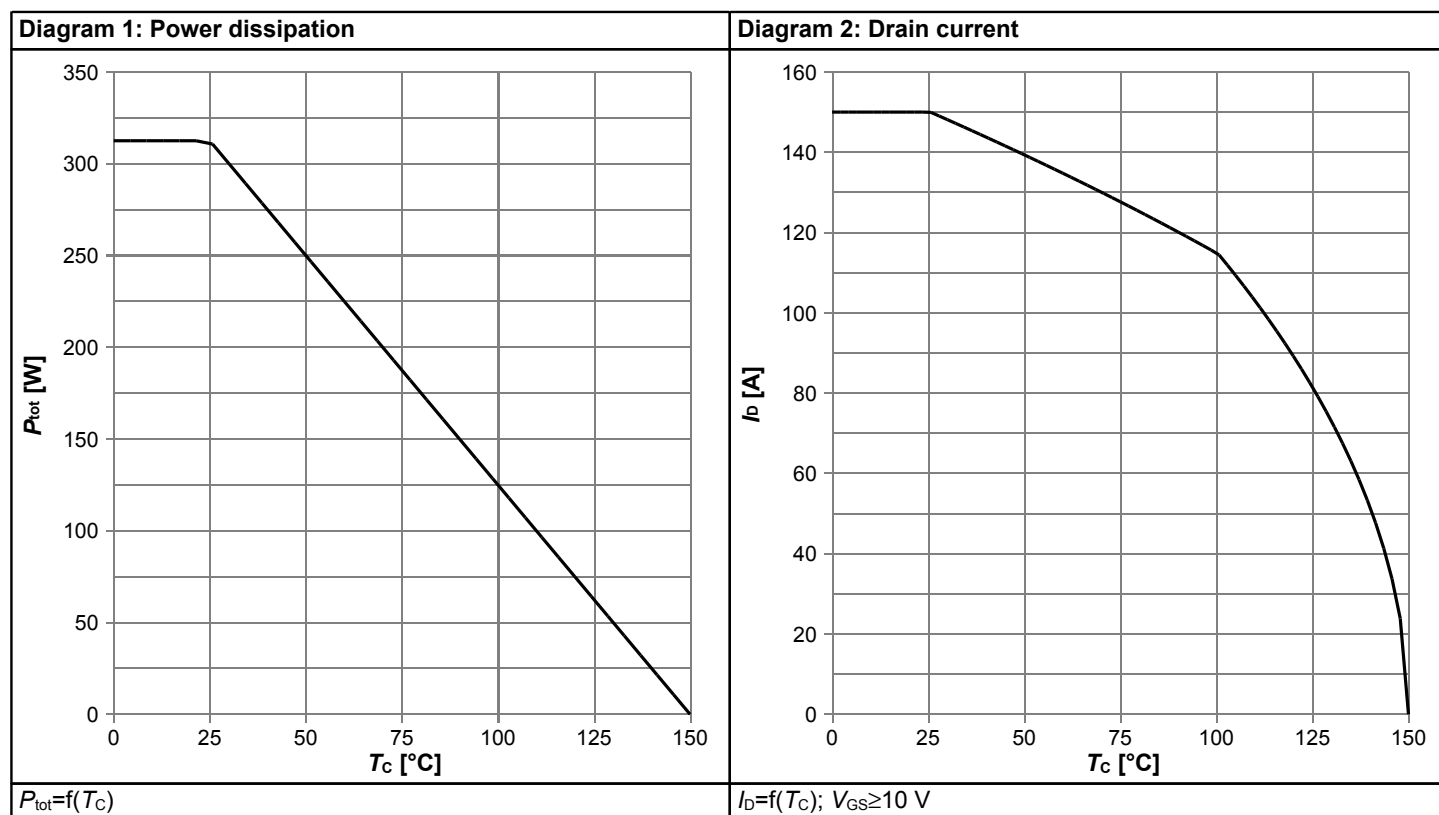
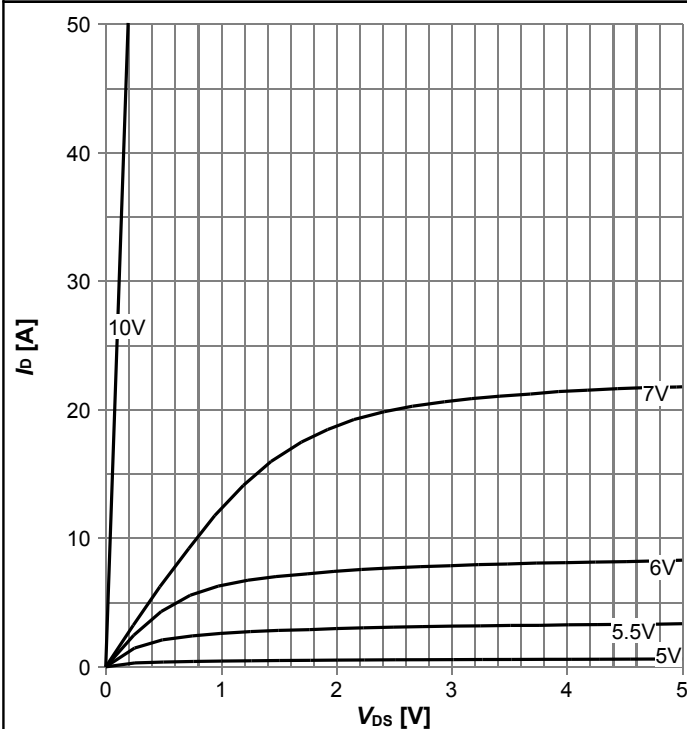
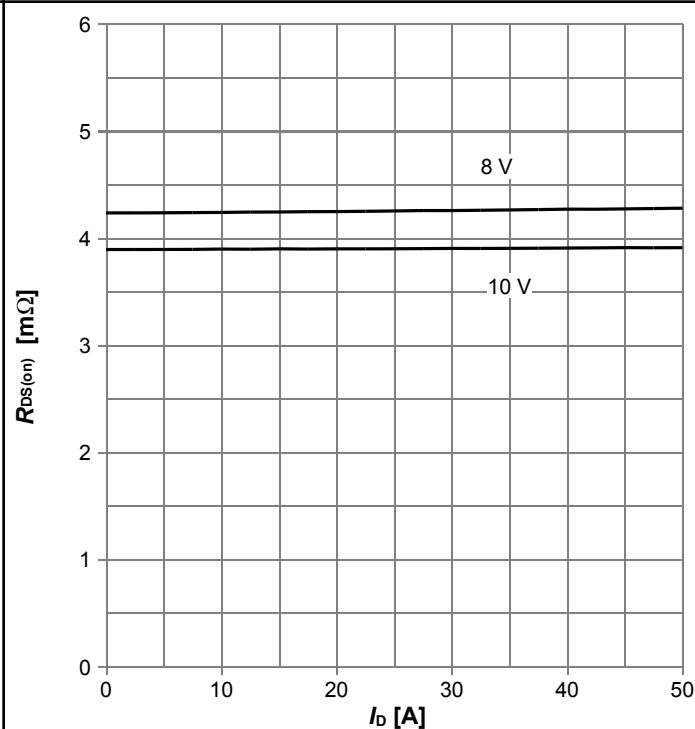


Diagram 5: Typ. output characteristics



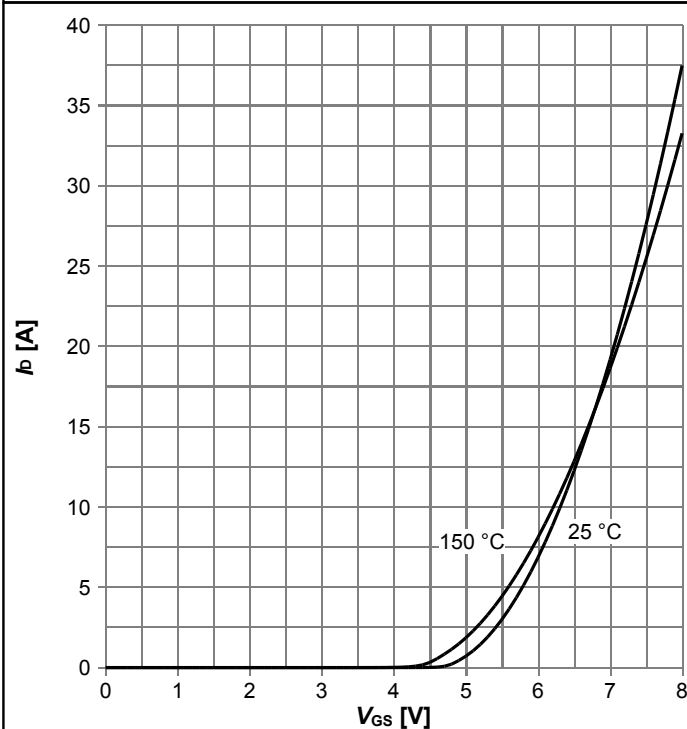
$I_D = f(V_{DS})$, $T_J = 25^\circ\text{C}$; parameter: V_{GS}

Diagram 6: Typ. drain-source on resistance



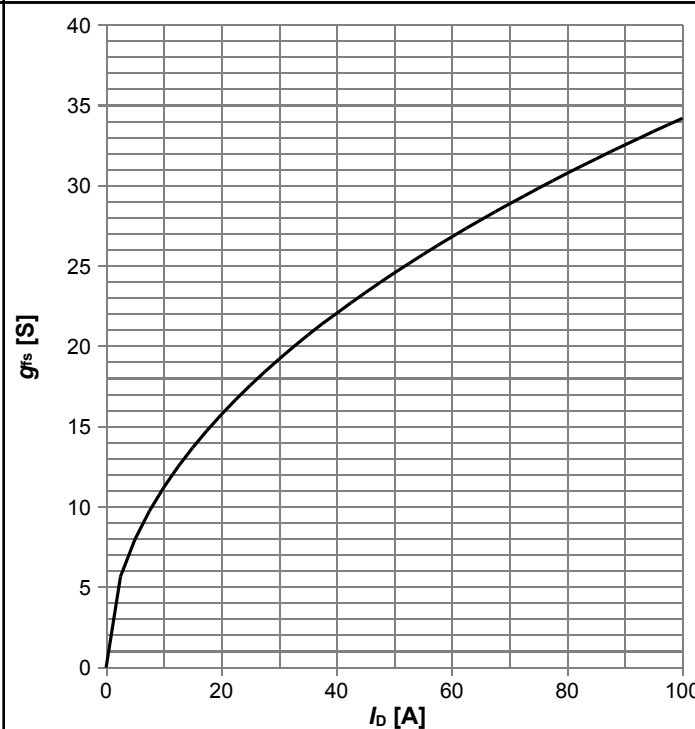
$R_{DS(on)} = f(I_D)$, $T_J = 25^\circ\text{C}$; parameter: V_{GS}

Diagram 7: Typ. transfer characteristics



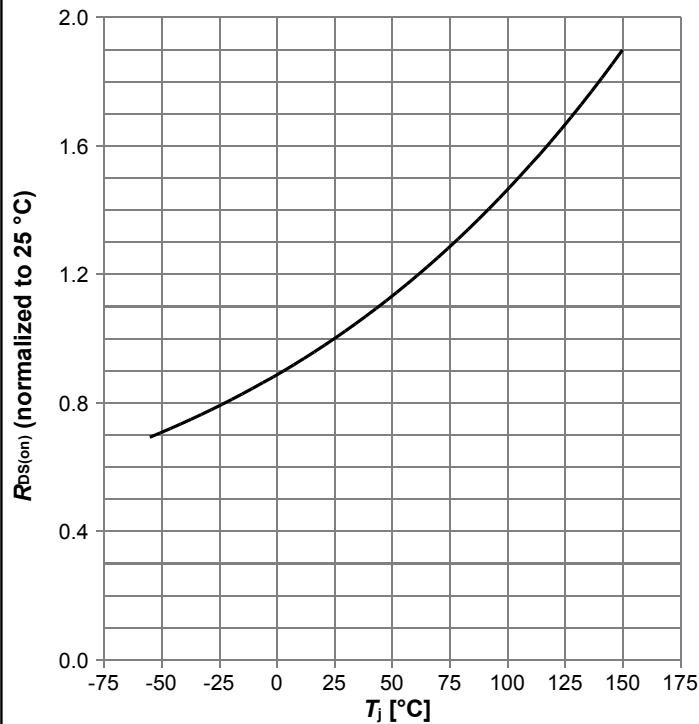
$I_D = f(V_{GS})$, $V_{DS} = 10\text{V}$; parameter: T_J

Diagram 8: Typ. forward transconductance



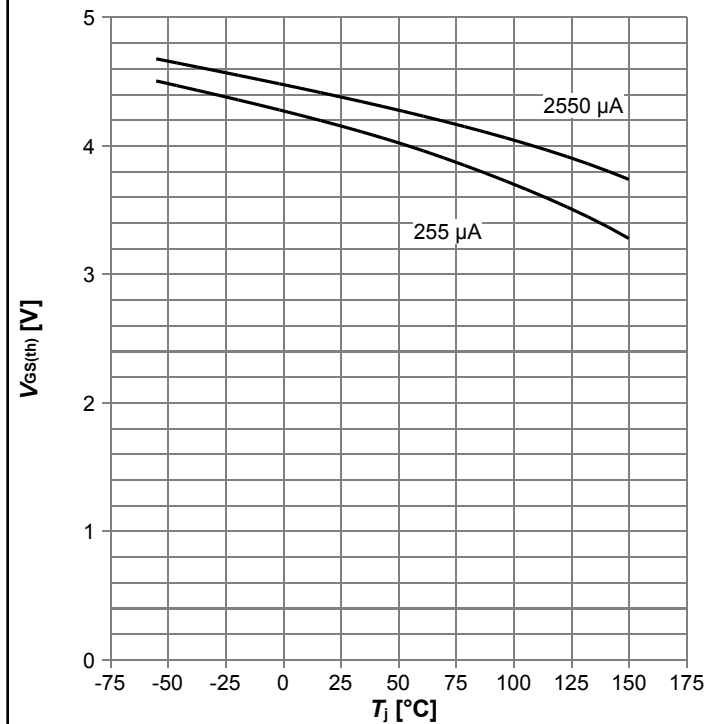
$g_{fs} = f(I_D)$, $V_{DS} = 6\text{V}$, $T_J = 25^\circ\text{C}$

Diagram 9: Normalized drain-source on resistance



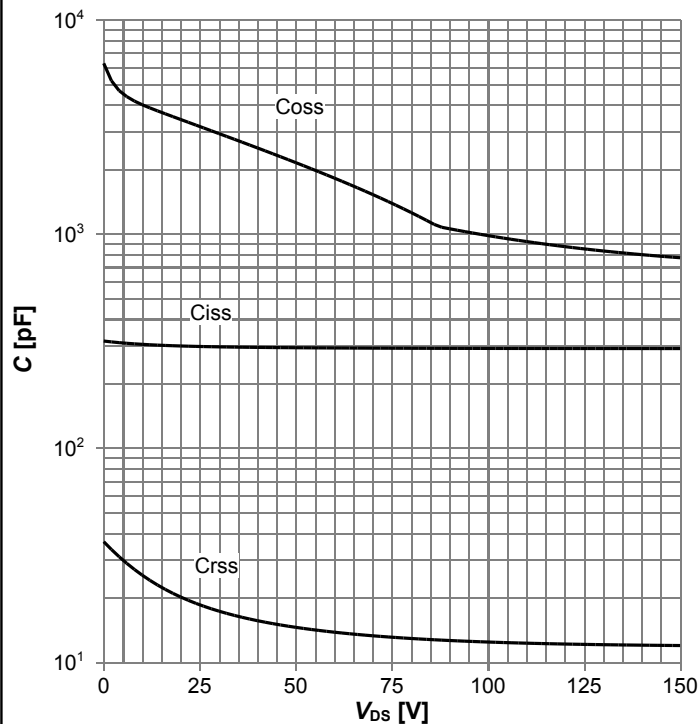
$R_{DS(on)} = f(T_j)$, $I_D = 100$ A, $V_{GS} = 10$ V

Diagram 10: Typ. gate threshold voltage



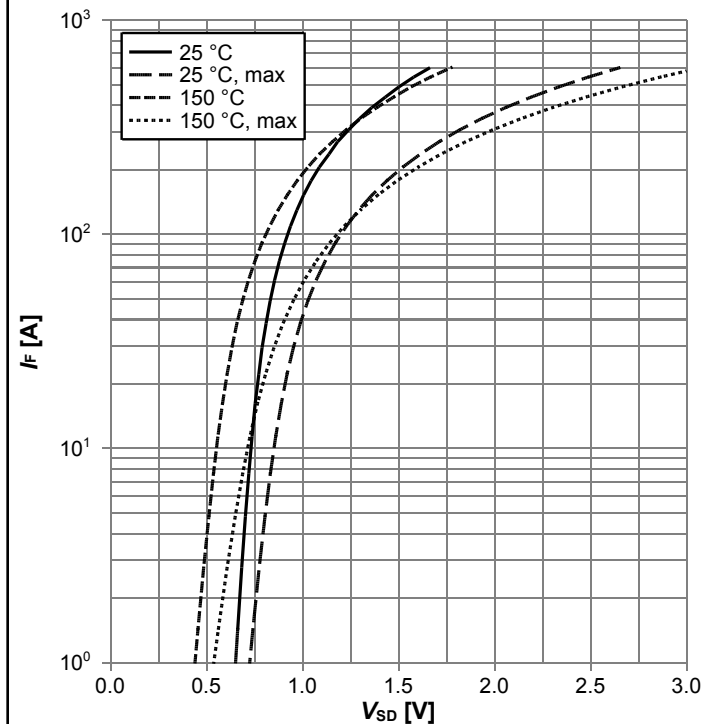
$V_{GS(th)} = f(T_j)$, $V_{GS} = V_{DS}$; parameter: I_D

Diagram 11: Typ. capacitances



$C = f(V_{DS})$; $V_{GS} = 0$ V; $f = 1$ MHz

Diagram 12: Forward characteristics of reverse diode

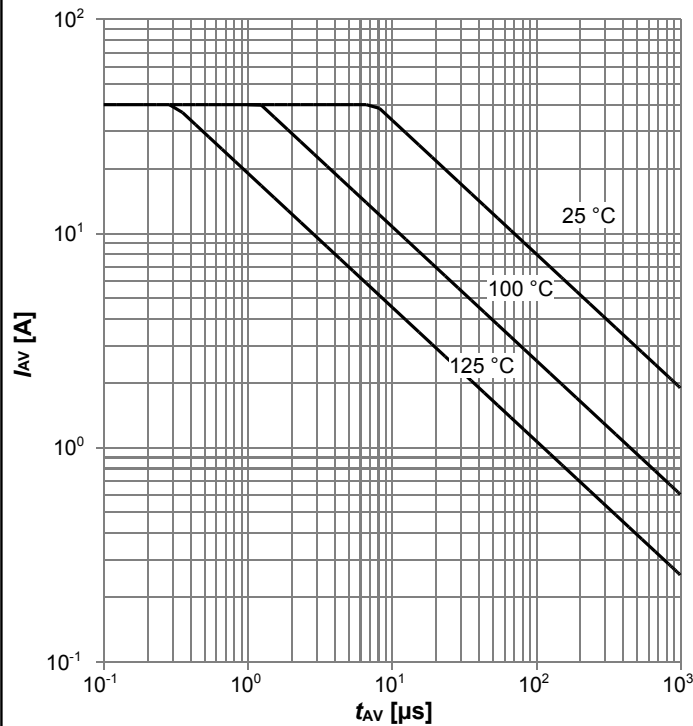


$I_F = f(V_{SD})$; parameter: T_j

OptiMOS™ 5 Linear FET, 150 V

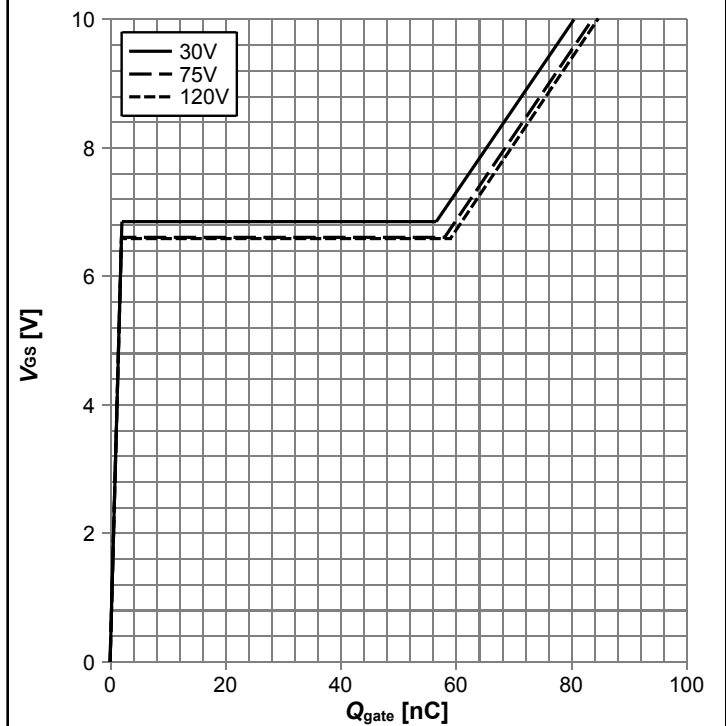
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Diagram 13: Avalanche characteristics



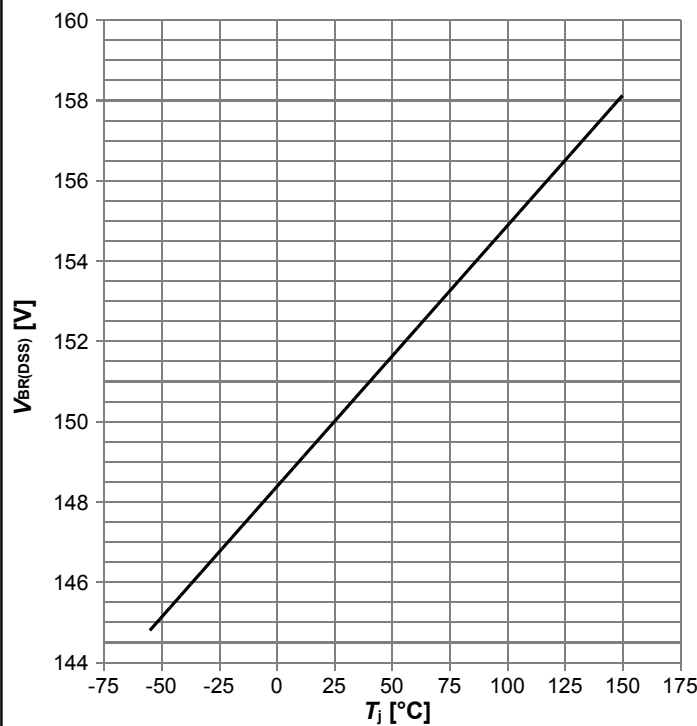
$I_{AS}=f(t_{AV})$; $R_{GS}=25\ \Omega$; parameter: $T_{j,start}$

Diagram 14: Typ. gate charge



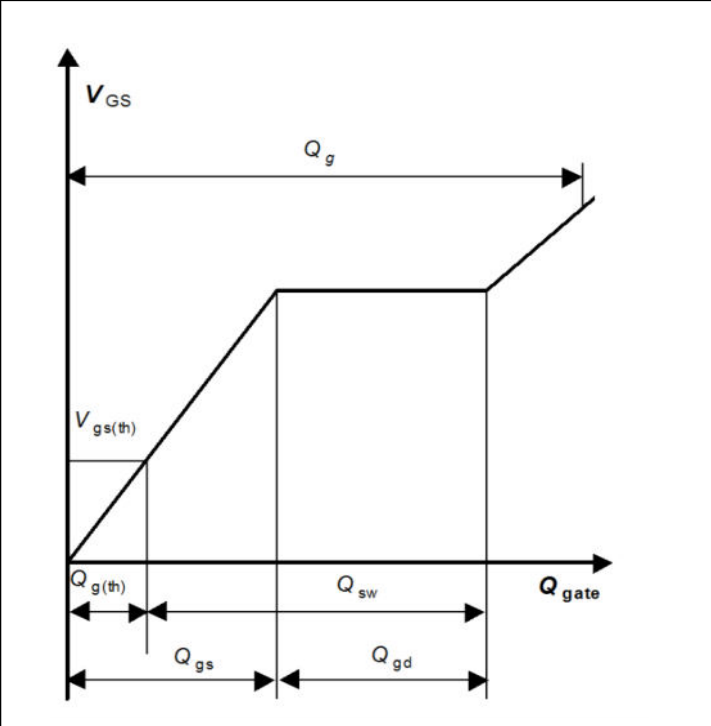
$V_{GS}=f(Q_{gate})$; $I_D=60\text{ A}$ pulsed, resistive load; parameter: V_{DD}

Diagram 15: Drain-source breakdown voltage



$V_{BR(DSS)}=f(T_J)$; $I_D=1\text{ mA}$

Diagram Gate charge waveforms



5 Package Outlines

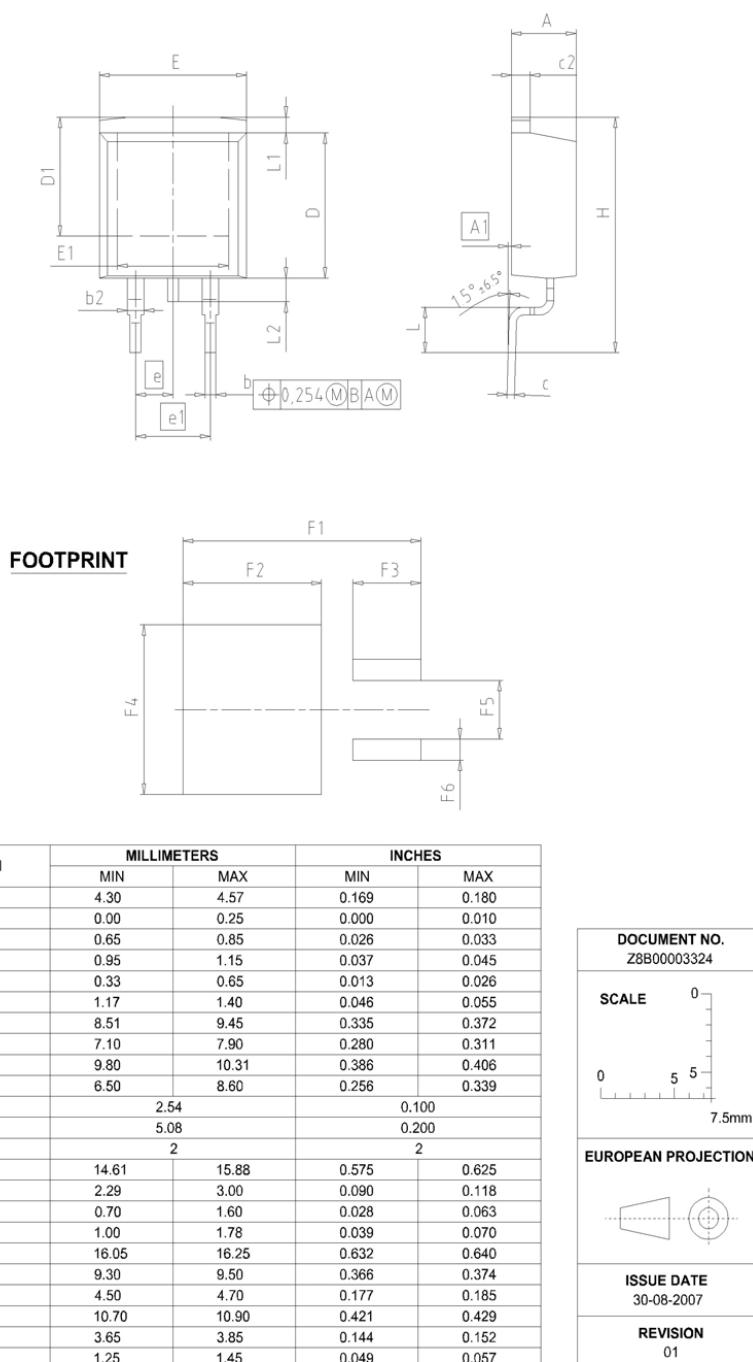


Figure 1 Outline PG-TO263-3, dimensions in mm/inches

Revision History

IPB048N15N5LF

Revision: 2022-09-09, Rev. 2.2

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.0	2017-03-29	Release of final version
2.1	2022-06-23	Update current rating, footnotes and skip condition "Operating and storage temperature".
2.2	2022-09-09	Update legend Diagram 7

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